Photo Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-005-9531

Inclosure Material:
Metal and glass
Overall Length:
Between 0.190 inches and 0.210 inches
Terminal Length:
0.500 inches
Overall Diameter:
Between 0.209 inches and 0.230 inches
Function For Which Designed:
Phototransistor
Internal Configuration:
Point contact
Mounting Method:
Terminal
Terminal Circle Diameter:
0.100 inches
Features Provided:
Hermetically sealed case
Semiconductor Material:
Gallium arsenide
Voltage Rating In Volts Per Characteristic:
2.0 reverse voltage, dc
Current Rating Per Characteristic:
200.00 milliamperes source cutoff current preset
Power Rating Per Characteristic:
6.0 milliwatts any acceptable preset
Maximum Operating Tempurature Per Measurement Point:
80.0 degrees celsius ambient air
Special Features:
Junction pattern arrangement: pn
Terminal Type And Quantity:
3 uninsulated wire lead
Shelf Life:
N/a
Unit Of Measure:
Demilitarization:
Yes - demil/mli
Fiig:
A110a0